

February 1999



FDN360P

Single P-Channel PowerTrench[™] MOSFET

General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Applications

- DC/DC converter
- Load switch
- Motor drives

Features

- -2 A, -30 V. $R_{DS(on)} = 0.080 \ \Omega \ @ V_{GS} = -10 \ V$ $R_{DS(on)} = 0.125 \ \Omega \ @ V_{GS} = -4.5 \ V.$
- Low gate charge (5nC typical).

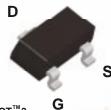
G

- Fast switching speed.
- High performance trench technology for extremely low R_{DS(ON)}.

D

S

• High power and current handling capability.



SuperSOT[™]-3

Absolute Maximum Ratings T_A = 25°C unless otherwise noted

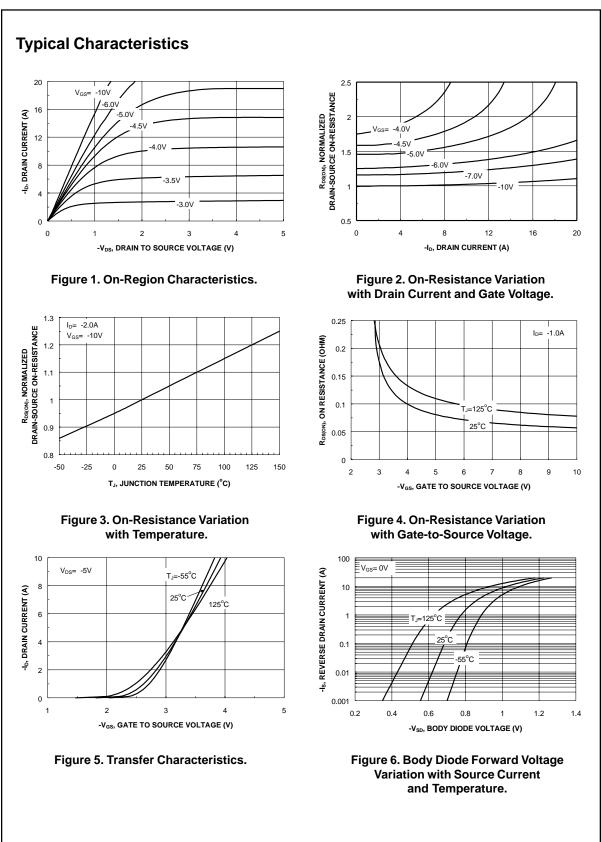
Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		<u>+</u> 20	V
ID	Drain Current - Continuous	(Note 1a)	-2	Α
	- Pulsed		-20	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C
Therma	I Characteristics			
R _{θJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	∘C/W

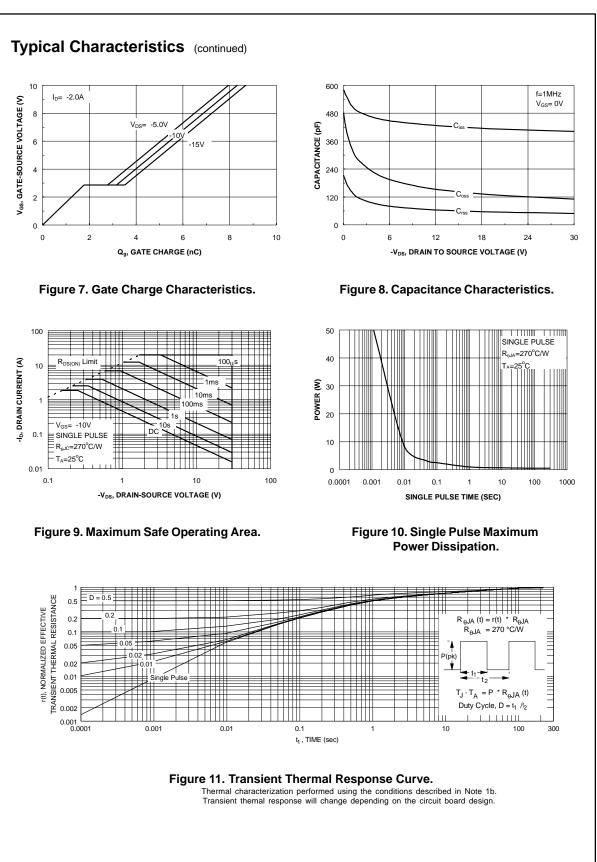
i θja	Thermal Resistance, sunction to Ambient		230	0/ ••
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

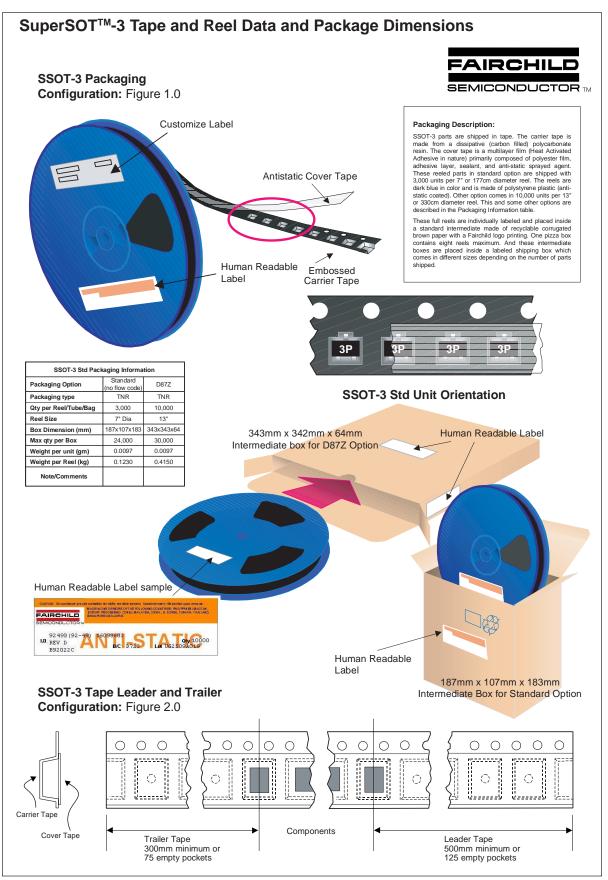
Package Outlines and Ordering Information

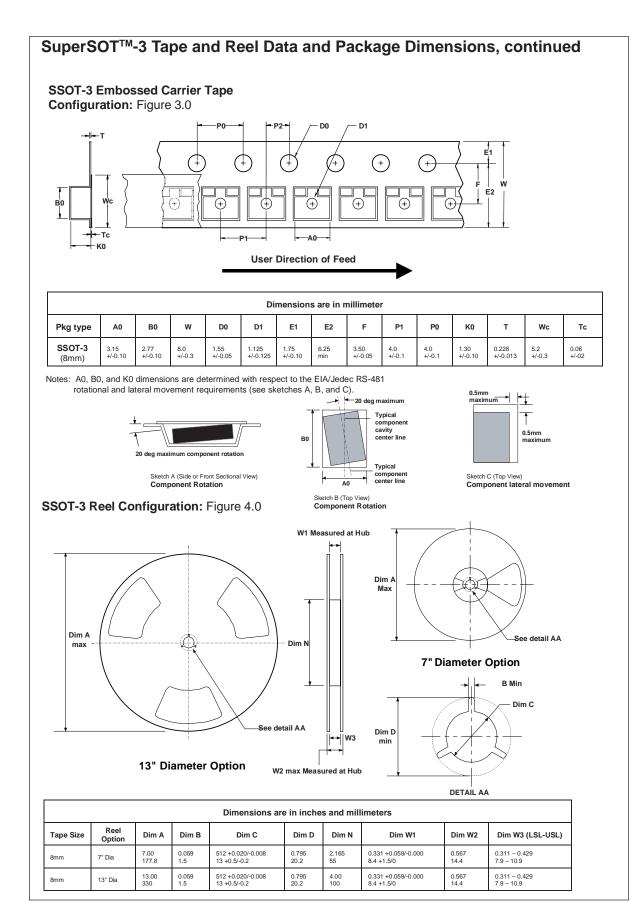
Device Marking	Device	Reel Size	Tape Width	Quantity
360	FDN360P	7"	8mm	3000 units

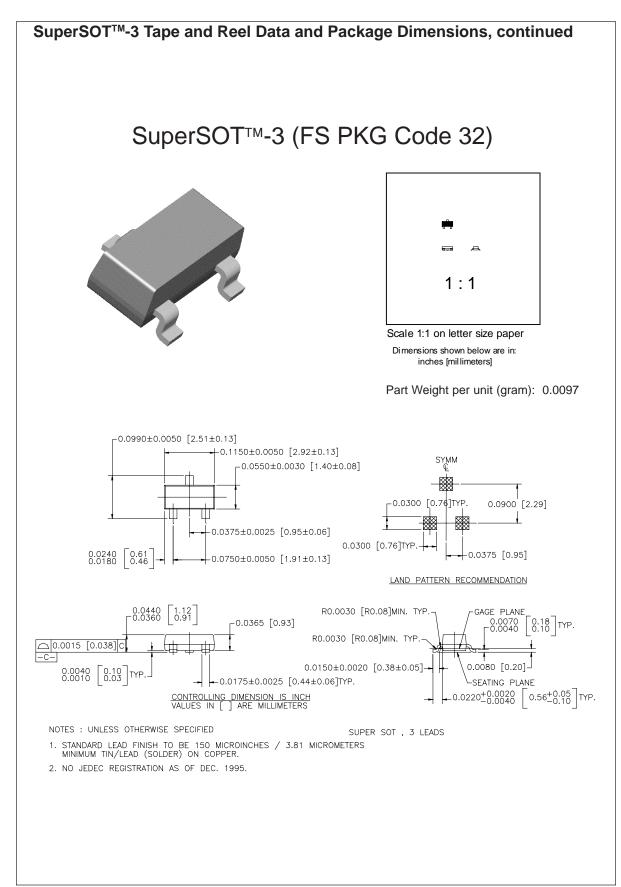
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = -250 \mu A$	-30			V
<u>A</u> BV⊡ss ∆TJ	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to 25° C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -24 V, V _{GS} = 0 V			-1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-1	-1.8	-3	V
<u>A</u> VGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu A$, Referenced to $25^{\circ}C$		-4		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -10 V, I_D = -2 A$ $V_{GS} = -10 V, I_D = -2 A, T_J=125 \circ C$ $V_{GS} = -4.5 V, I_D = -1.5 A$		0.060 0.080 0.095	0.080 0.136 0.125	Ω
D(on)	On-State Drain Current	$V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	-20			Α
FS	Forward Transconductance	$V_{DS} = -5 V, I_{D} = -2 A$		5.5		S
Dynamia	c Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -15 V, V_{GS} = 0 V,$		420		pF
Coss	Output Capacitance	f = 1.0 MHz		140		pF
	Reverse Transfer Capacitance	-		60		pF
	-					
	Turne On Delay Time a		<u> </u>	0	40	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -15$ V, $I_D = -1$ A, V _{GS} = -10 V, R _{GEN} = 6 Ω		9	18	ns
t _r	Turn-On Rise Time			8	16	ns
d(off)	Turn-Off Delay Time	_		18	29	ns
f	Turn-Off Fall Time			6	12	ns
Q _g	Total Gate Charge	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -2 \text{ A},$ $V_{GS} = -10 \text{ V}.$		5	7	nC
Q _{gs}	Gate-Source Charge	-		1.7		nC
Q _{gd}	Gate-Drain Charge			1.8		nC
Drain-Sc	purce Diode Characteristics a	and Maximum Ratings	T	1		1
ls	Maximum Continuous Drain-Source	Diode Forward Current			-0.42	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = -0.42 A$ (Note 2)		-0.75	-1.2	V
	sum of the junction-to-case and case-to-ambien the drain pins. $R_{a,c}$ is guaranteed by design whil			defined as	the solder	mounting
, M	•••• •	 b) 270°C/W when mounted on a 0.001 in² pad of 2 oz. Cu. 				
0 0						











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